# 6<sup>th</sup> Generation CoolSiC<sup>™</sup>

### IDH06G65C6



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# 1 Maximum ratings

Table 3 Maximum ratings

Damana ahan	Complete 1	Values			<b> </b>	
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition
	$I_F$	-	_	6		$T_C \le 145 ^{\circ}\text{C}, D = 1$
Continuous forward current		-	_	9		$T_C \le 125 ^{\circ}\text{C}, D = 1$
		-	_	16		$T_C \le 25 ^{\circ}\text{C}, D = 1$
Surge-repetitive forward current, sine halfwave <sup>1</sup>	$I_{F,RM}$	-	_	26	A	$T_C = 25  ^{\circ}\text{C}, t_p = 10  \text{ms}$
Surge non-repetitive forward	,	_	_	38		$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
current, sine halfwave	$I_{F,SM}$	_	_	30		$T_C = 150 ^{\circ}\text{C}, t_\rho = 10 \text{ms}$
Non-repetitive peak forward current	I <sub>F,max</sub>	-	-	410		$T_C$ = 25 °C, $t_p$ = 10 μs
:24	( :2 -1+	-	_	7.2	A2-	$T_C = 25 ^{\circ}\text{C}, t_p = 10 \text{ms}$
i <sup>2</sup> t value	∫i²dt	_	_	4.6	A <sup>2</sup> s	$T_C = 150  ^{\circ}\text{C},  t_{\rho} = 10  \text{ms}$
Repetitive peak reverse voltage	V <sub>RRM</sub>	_	_	650	٧	<i>T<sub>c</sub></i> = 25 °C
Diode dv/dt ruggedness	dv/dt	-	_	150	V/ns	V <sub>R</sub> = 0480 V
Power dissipation	P <sub>tot</sub>	_	_	54	W	$T_C = 25^{\circ}\text{C}, R_{thJC,max}$
Operating and storage temperature	$T_j$ $T_{stg}$	-55	-	175	°C	-
Mounting torque	_	_	_	70	Ncm	M3 screw

# 2 Thermal characteristics

Table 4 Thermal characteristics (PG-TO-220-2)

Davamatav	Complete		Values		l lm!s	Unit Note/Test condition
Parameter	Symbol	Min.	Тур.	Max.	Unit	
Thermal resistance, junction- case	$R_{thJC}$	-	1.7	2.8	12 /\AI	_
Thermal resistance, junctionambient	$R_{thJA}$	_	_	62	K/W	leaded
Soldering temperature, wavesoldering only allowed at leads	$\mathcal{T}_{sold}$	-	-	260	°C	1.6 mm (0.063 in.) from case for 10 s

<sup>&</sup>lt;sup>1</sup> The surge-repetitive forward current test was performed with 1000 pulses (half-wave rectified sine with the 10 ms period).

Final Datasheet

3 Rev. 2.0, 2017-05-23



# 3 Electrical characteristics

### 3.1 Static characteristics

 Table 5
 Static characteristics

Davamatav	Complete		Values Unit Note/Test conditio			Note/Test condition
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test condition
DC blocking voltage	$V_{DC}$	650	_	_		<i>T<sub>j</sub></i> = 25 °C
Diada famuard valtaga	17	_	1.25	1.35	V	$I_F = 6 \text{ A}, T_j = 25 ^{\circ}\text{C}$
Diode forward voltage	$V_F$	_	1.5	_		$I_F = 6 \text{ A}, T_j = 150 ^{\circ}\text{C}$
		_	0.6	20		$V_R = 420 \text{ V}, T_j = 25 \text{ °C}$
Reverse current	urrent $I_R$ $-$ 20 $ \mu A$	μΑ	$V_R = 420 \text{ V}, T_j = 125 \text{ °C}$			
		_	46	_		$V_R = 420 \text{ V}, T_j = 150 \text{ °C}$

#### 3.2 AC characteristics

Table 6 AC characteristics

Development	Values Unit Note/Took		Note/Test Condition			
Parameter	Symbol	Min.	Тур.	Max.	Unit	Note/Test Condition
Total capacitive charge	$Q_c$	_	9.6	_	nC	$V_R$ = 400 V, $T_j$ = 150 °C, di/dt = 200 A/µs, $I_F \le I_{F,MAX}$
		_	302	_		$V_R = 1 \text{ V}, f = 1 \text{ MHz},$ $T_j = 25 \text{ °C}$
Total capacitance	С	_	18	-	pF	$V_R$ = 300 V, $f$ = 1 MHz, $T_j$ = 25 °C
		-	17	-		$V_R$ = 600 V, $f$ = 1 MHz, $T_j$ = 25 °C



# 4 Diagrams

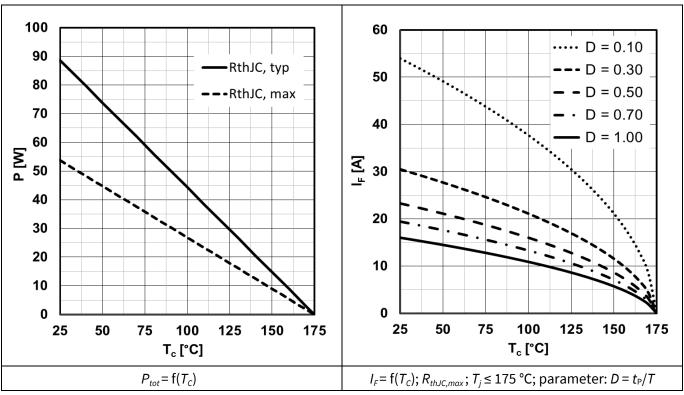


Figure 1 Power dissipation

Figure 2 Max. forward current

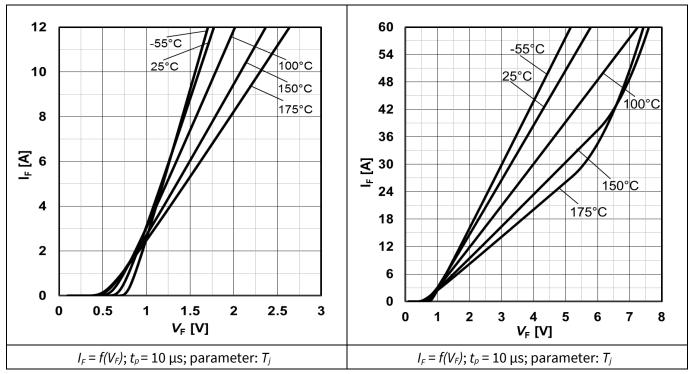


Figure 3 Typ. forward characteristics

Figure 4 Typ. forward characteristics in surge current



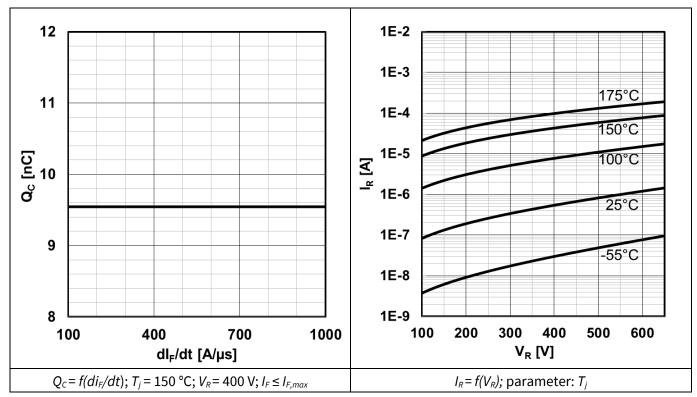


Figure 5 Typ. cap. charge vs. current slope

Figure 6 Typ. reverse current vs. reverse voltage

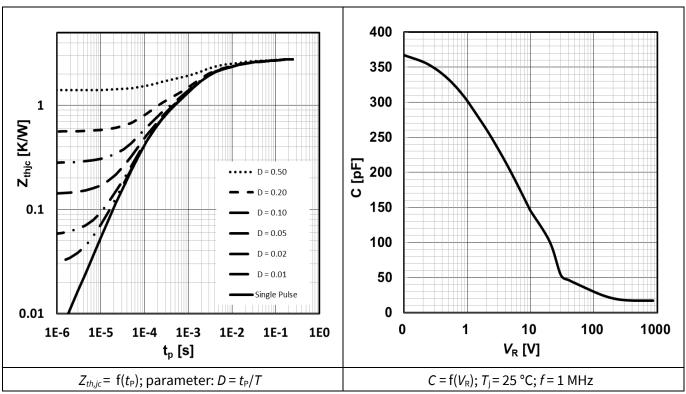


Figure 7 Max. transient thermal impedance

Figure 8 Typ. capacitance vs. reverse voltage



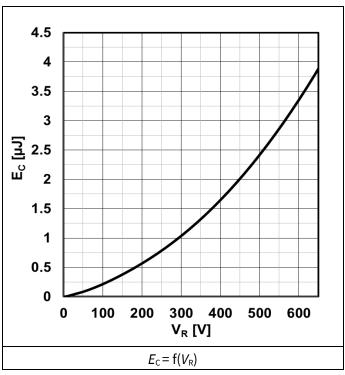


Figure 9 Typ. capacitance stored energy

# 5 Simplified forward characteristic

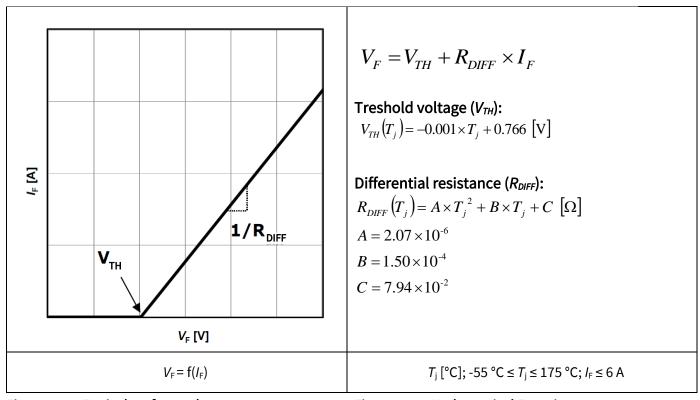


Figure 10 Equivalent forward current curve

Figure 11 Mathematical Equation



# 6 Package outlines

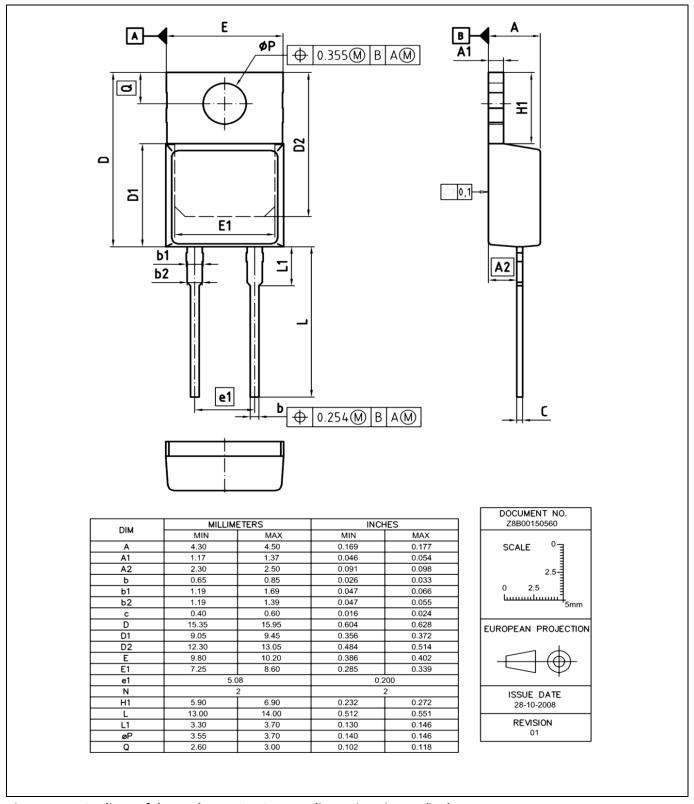


Figure 12 Outlines of the package PG-TO220-2, dimensions in mm/inches

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# **Revision History**

# Major changes since the last revision

Revision	Date	Subject (major changes since last revision)					
2.0	2017-05-23	Release of final version					

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